

L Number	Hits	Search Text	DB	Time stamp
1	2811689	memory or storage	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/15 11:38
2	14611	(memory or storage) and cell with transistor with capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/15 11:39
3	628	((memory or storage) and cell with transistor with capacitor) and refresh\$5 with transistor with cell	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/15 11:40
4	313	((memory or storage) and cell with transistor with capacitor) and normal with transistor with cell	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/15 11:40
5	24	((((memory or storage) and cell with transistor with capacitor) and normal with transistor with cell) and refresh\$5 near3 amplifier	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/15 11:41

L Number	Hits	Search Text	DB	Time stamp
1	2811689	memory or storage	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/15 14:01
2	14611	(memory or storage) and cell with transistor with capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/15 14:03
3	628	((memory or storage) and cell with transistor with capacitor) and refresh\$5 with transistor with cell	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/15 14:04
4	57	((((memory or storage) and cell with transistor with capacitor) and refresh\$5 with transistor with cell) and normal with transistor with cell	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/15 14:05
5	18	(((((memory or storage) and cell with transistor with capacitor) and refresh\$5 with transistor with cell) and normal with transistor with cell) and refresh\$5 near3 amplifier	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/15 14:05

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1	2811689	memory or storage	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/15 15:27
2	14611	(memory or storage) and cell with transistor with capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/15 15:30
3	400	((memory or storage) and cell with transistor with capacitor) and chang\$5 with (potential or voltage or level) with plate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/15 15:38
4	2	((memory or storage) and cell with transistor with capacitor) and chang\$5 with (potential or voltage or level) with plate) and belt with plate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/15 15:34
5	4	((memory or storage) and cell with transistor with capacitor) and chang\$5 with (potential or voltage or level) with plate) and (correct\$5 or compensat\$5) with (voltage or potential or level) with leak\$5 with capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/15 15:36
6	189	((memory or storage) and cell with transistor with capacitor) and chang\$5 with (potential or voltage or level) with plate with capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/15 15:39
7	20	((memory or storage) and cell with transistor with capacitor) and chang\$5 with (potential or voltage or level) with plate with capacitor with current	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/15 15:40